General purpose (dual digital transistors)

UMH11N / IMH11A

●Features

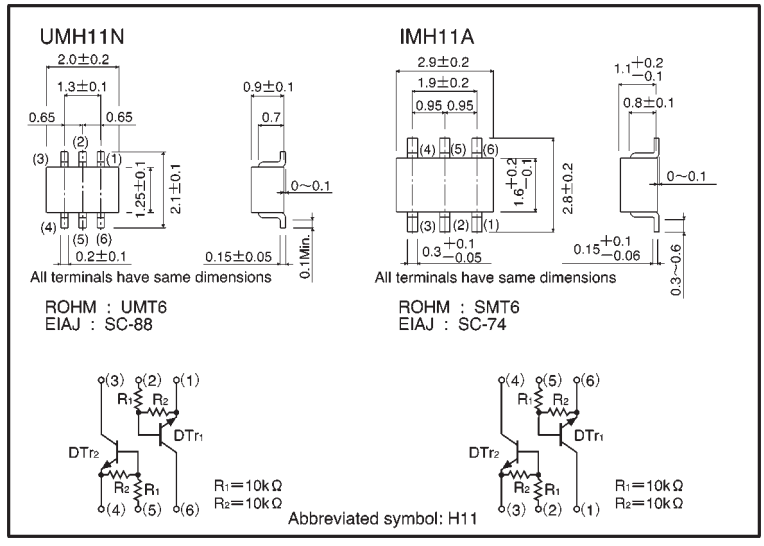
1) Two DTC114E chips in a UMT or SMT package.
2) Mounting possible with UMT3 or SMT3 automatic mounting machines.
3) Transistor elements are independent, eliminating interference.
4) Mounting cost and area can be cut in half.

●Structure

Epitaxial planar type
NPN silicon transistor
(Built-in resistor type)

The following characteristics apply to both DTr_1 and DTr_2.

●External dimensions (Units: mm)



●Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits	Unit
Supply voltage		V_{CC}	50	V
Input voltage		V_{IN}	40	V
			−10	
Output current		I_O	50	mA
Collector current		$I_{C(Max.)}$	100	mA
Power dissipation	UMH11N	Pd	150 (TOTAL)	mW ∗1
	IMH11A		300 (TOTAL)	mW ∗2
Junction temperature		Tj	150	℃
Storage temperature		Tstg	−55~+150	℃

∗1 120mW per element must not be exceeded.
∗2 200mW per element must not be exceeded.

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Input voltage	$V_{I(off)}$	—	—	0.5	V	V_{CC}=5V, I_O=100 μA
	$V_{I(on)}$	3	—	—		V_O=0.3V, I_O=10mA
Output voltage	$V_{O(on)}$	—	0.1	0.3	V	I_O/I_I=10mA/0.5mA
Input current	I_I	—	—	0.88	mA	V_I=5V
Output current	$I_{O(off)}$	—	—	0.5	μA	V_{CC}=50V, V_I=0V
DC current gain	G_I	30	—	—	—	V_O=5V, I_O=5mA
Transition frequency	f_T	—	250	—	MHz	V_{CE}=10mA, I_E=−5mA, f=100MHz ✻
Input resistance	R_1	7	10	13	kΩ	—
Resistance ratio	R_2/R_1	0.8	1	1.2	—	—

✻ Transition frequency of the device

●Packaging specifications

Part No.	Packaging type	Taping	
	Code	TN	T110
	Basic ordering unit (pieces)	3000	3000
UMH11N		○	—
IMH11A		—	○

●Electrical characteristic curves

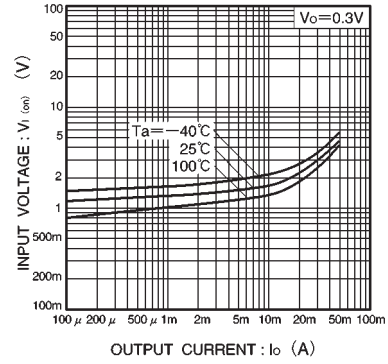


Fig.1 Input voltage vs. output current (ON characteristics)

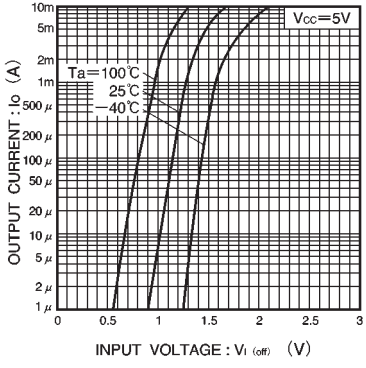


Fig.2 Output current vs. input voltage (OFF characteristics)

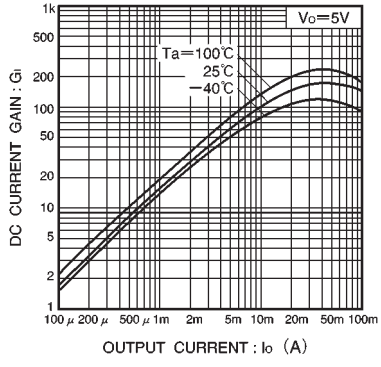


Fig.3 DC current gain vs. output current

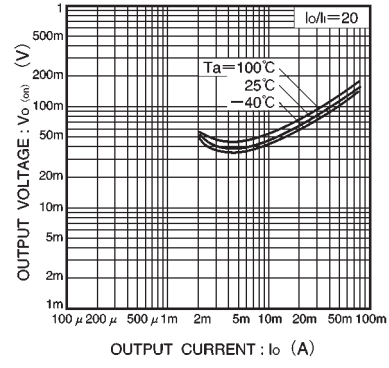


Fig.4 Output voltage vs. output current